

Issue Date: 29 April 2015

Title of Chang	ge:	SOD-123 devices Cu wire qualification at ON Semiconductor, Leshan, China facility.							
Proposed first ship date:		5 August 2015							
Contact information:			Contact your local ON Semiconductor Sales Office or <coleen.long@onsemi.com></coleen.long@onsemi.com>						
Samples:		Cont	Contact your local ON Semiconductor Sales Office						
Additional Re	cional Reliability Data: Contact your local ON Semiconductor Sales Office or <zz.cheng@onsemi.com></zz.cheng@onsemi.com>								
Type of notif	ication:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <pcn.support@onsemi.com>.</pcn.support@onsemi.com>							
Change Part	Identification:	At the expiration of this FPCN devices will be assembled with Cu Wire at ON Semiconductor's existing Leshan facility. Devices with Cu Wire will have date code of WW31, 2015 or later.							
Change category(s): Wafer Fab Change Assembly Change Test Change			 Manufacturing Site Change/Addition Manufacturing Process Change Material Change 			Product specific change Datasheet/Product Doc change Shipping/Packaging/Marking Other:			
Sites Affected: ☐ All site(s) ☐ not applicable ⊠ ON Semiconductor site(s) : ☐ External Foundry/Subcon site(s):			Site 1 Site ON Leshan, China		<u>Site</u>	<u>2 2</u>			
Description and Purpose: ON Semiconductor is pleased to announce the completion of Cu Wire qualification for the impacted devices at ON Semiconductor's Leshan, China facility. The impacted devices are currently assembled at the ON Semiconductor Leshan, China facility with Au Wire. At the expiration of this PCN, these devices will be built with Cu Wire at the same site. There is no change in package outline or electrical performance of the parts they continue to fully meet datasheet specifications.									
Reliability Da Qual vehicle BAT54T1G	ita Summary: :								
Test			Condition	Interval		Results			
HTRB	Tj=150C or opera	ating T	j 80% V bias (JA108)	1008 H	rs	0/231			
HTSL	Ta=150C, or 175C based on datasheet max TA storage			1008 Hrs		0/231			
IOL	Ta=+25°C, delta1	°C, deltaTj=100°C max, 2min on/off for 15000 cyc Cycle 0/231			0/231				
TC Temp = -65°C to +150°C;			C; for 1000 cycles (JA104B)	1000 Cycle		0/231			
AC	Temp = +121°C;	RH =1(00%, (JA110)	96 Hrs		0/231			

Temp = +85°C; RH = 85%, 80% V bias (JA101)

TS=260C, Tdwell=10 sec. (Jedec B-106)

H3TRB

RSH

1008 Hrs

0/231

0/90



MMSD103T1G

Test	Condition	Interval	Results				
HTRB	Tj=150C or operating Tj 80% V bias (JA108)	1008 Hrs	0/231				
HTSL	Ta=150C, or 175C based on datasheet max TA storage	1008 Hrs	0/231				
IOL	Ta=+25°C, deltaTj=100°C max, 2min on/off for 15000 cyc	15000Cycle	0/231				
тс	Temp = -65°C to +150°C; for 1000 cycles (JA104B)	1000 Cycle	0/231				
AC	Temp = +121°C; RH =100%, (JA110)	96 Hrs	0/231				
H3TRB	Temp = +85°C; RH = 85%, 80% V bias (JA101)	1008 Hrs	0/231				
RSH	TS=260C, Tdwell=10 sec. (Jedec B-106)		0/90				
Electrical Characteristic Summary: Electrical Characteristics are not impacted.							
List of Affected Standard Parts:							
MMSD301T1G							
MMSD701T1G							
MMSD4148T3G							
MMSD4148T1G							